

Notice of References Cited	Application/Control No. 10/817,618		Applicant(s)/Patent Under Reexamination SHENAI-KHATKHATE ET AL.	
	Examiner B. Chen		Art Unit 1762	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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NON-PATENT DOCUMENTS

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	V	Son, Jong-Hoon, et al. "Growth Rate and Microstructure of Copper Thin Films ..." Thin Solid Films 335 (1998) pp. 229-236.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.